TOSHIBA SCHOTTKY BARRIER RECTIFIER SCHOTTKY BARRIER TYPE

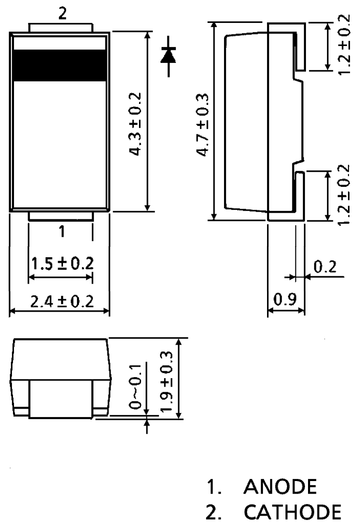
U2FWJ44M

SWITCHING TYPE POWER SUPPLY APPLICATION

PORTABLE EQUIPMENT BATTERY APPLICATION

- Low Forward Voltage : $V_{FM} = 0.45$ V (Max.)
- Average Forward Current : $I_{F\,(AV)} = 2.0$ A
- Repetitive Peak Reverse Voltage : $V_{RRM} = 30$ V
- Surface Mounting Plastic Mold Package

Unit in mm



JEDEC	—
EIAJ	—
TOSHIBA	3-4D1A

Weight : 0.06 g

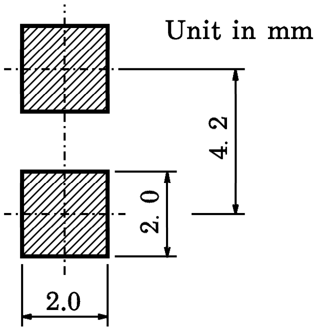
MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	30	V
Average Forward Current	$I_{F\,(AV)}$	2.0	A
Peak One Cycle Surge Forward Current (Non-Repetitive)	I_{FSM}	60 (50Hz)	A
Junction Temperature	T_j	−40~125	°C
Storage Temperature Range	T_{stg}	−40~125	°C

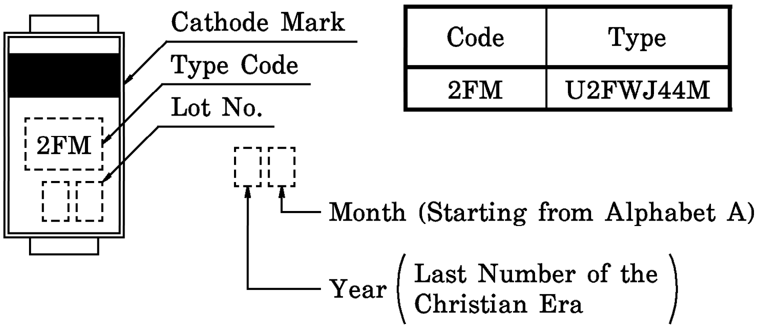
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	V_{FM}	$I_{FM} = 2.0$ A	—	—	0.45	V
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = 30$ V	—	—	500	μA
Junction Capacitance	C_j	$V_R = 10$ V, f = 1.0 MHz	—	125	—	pF
Thermal Resistance (Junction to Ambient)	$r_{th\,(j\text{-}a)}$	On ceramic substrate	—	—	60	°C / W
		On glass-epoxy substrate	—	—	145	

Standard Soldering Pad



MARKING



Code	Type
2FM	U2FWJ44M

961001EAA2

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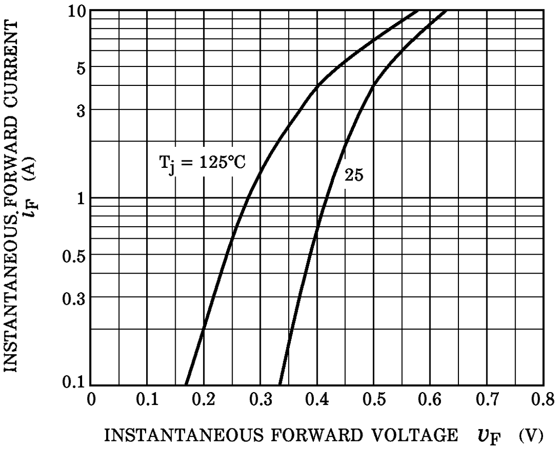
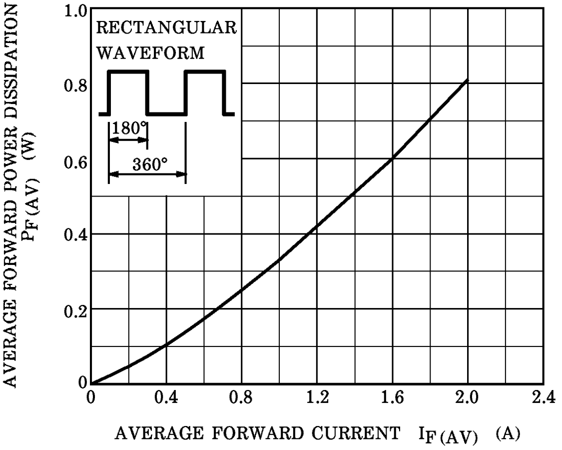
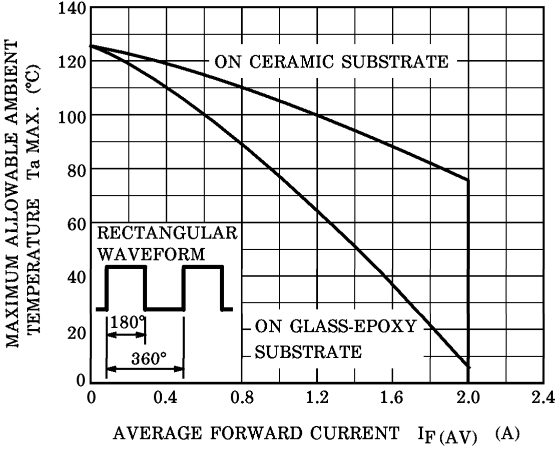
i_F – v_F



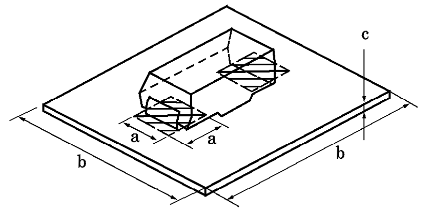
$P_{F(AV)}$ – $I_{F(AV)}$



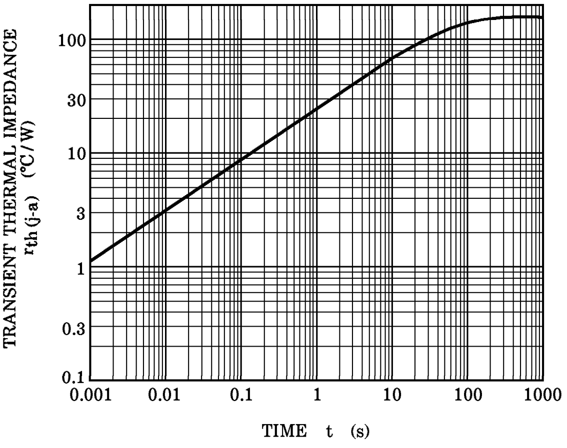
Ta MAX. – $I_{F(AV)}$



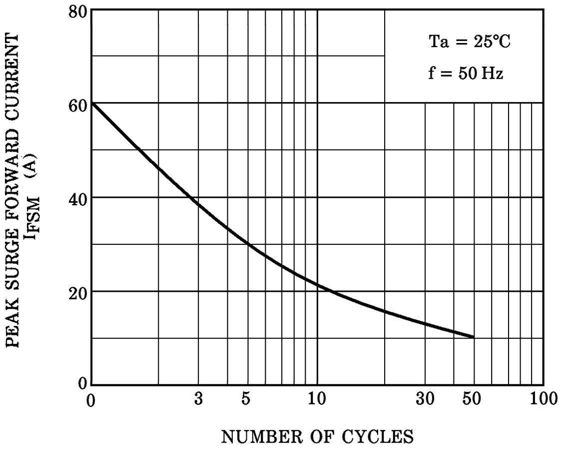
	ON CERAMIC SUBSTRATE	ON GLASS-EPOXY SUBSTRATE
Soldering land : a	2 mm × 2 mm	6 mm × 6 mm
Substrate size : b	50 mm × 50 mm	50 mm × 50 mm
Substrate thickness : c	0.64 mm	1.6 mm



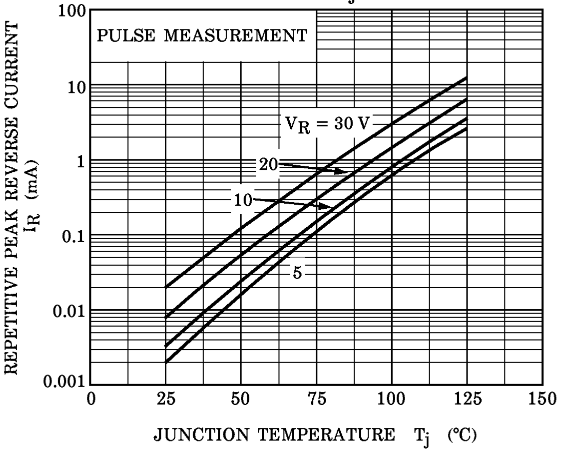
$r_{th\,(j\text{-}a)}$ – t



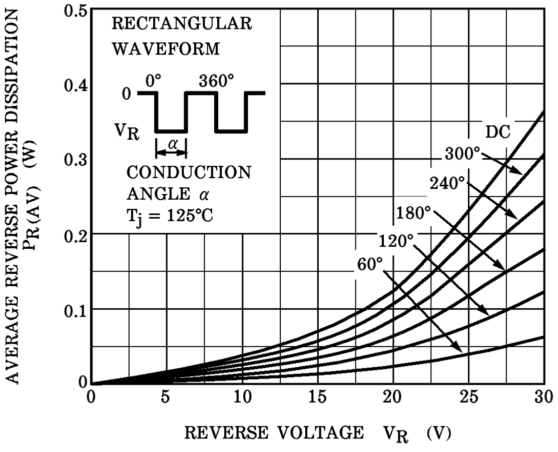
SURGE FORWARD CURRENT (NON-REPETITIVE)



$I_R - T_j$ (TYPICAL)



$P_{R(AV)} - V_R$ (TYPICAL)



$C_j - V_R$ (TYPICAL)